Non-Silicon Based Nano Fab Center

October 14, 2003

- <u>Location</u>

  East Suwon, KyungGi province 40Km away from Seoul
- 40,000㎡ Land will be used for Fab facilities
- Consortium of 6 organizations

  - 4 Universities (Seoul National Univ. / Hanyang Univ./ SungkyunKwan Univ. / Ajou Univ.)

  - 2 Research Institutes (KIST, KETI)

■ Network

- More than 20 companies participated in investment and collaboration

- Will be expanded further for Domestic and Global Network

■ Facilities

1. Fab Building(3300㎡ Clean Room) : 2005. June
    - Unit Process
    - Device Integration
    - Measurement and Analysis
    - Equipment Development
2. R&D Building : 2005. Dec
3. Industrial Building for Venture Companies

    : 2006. Dec

■ Technology

- Process Capability: MBE, MOCVD based process
- Electronic Device: HEMT, MMIC
- Optoelectronic Device : LD, LED, IR
- Nano Sensor
- Nano Device for Display Application
  : LCD, PDP, FED, CNT

Future Plan

1. Fab facilities will be constructed at the end of 2005

2. Process service will start at 2006
   (compound semiconductor, nano device)
   - Unit process
   - Foundry service

3. Strong network will be established (Domestic,Global)

- Universities
- Companies
- Research Institutes

4. R&D Building, Venture Building will contribute to technical transfer and industrialization.